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preventing at least some of said electrically chargeable particles from reaching said substrate.

53. (Once amended) A method of processing a semiconductor device, comprising:
- depositing a dielectric layer over a semiconductor substrate, wherein said step of depositing a dielectric layer comprises depositing a dielectric layer using a organic precursor;
 - allowing electrically chargeable particles to occur in said dielectric layer, wherein said step of allowing electrically chargeable particles to occur in said dielectric layer comprises allowing an organic component of said organic precursor to deposit in said dielectric layer;
 - allowing some diffusion of said electrically chargeable particles; and
 - preventing at least some of said electrically chargeable particles from reaching said substrate, wherein said preventing step comprises layering a barrier over said substrate using a non-organic precursor prior to said step of depositing a dielectric layer.

A marked-up version of these claims appears in Appendix 1 of this Amendment and Response.

REMARKS

Claims 52-64 are pending.

Claims 52-64 are rejected.

Claims 52-53 are amended

Applicants request the reconsideration of claims 52-64.

I. Rejection of claim under §112

Claim 60 refers to a “generally insulative material” and a “generally conductive element” that is “generally laterally coextensive” with an intervening insulating region. The Examiner argued that the term “generally” lacks support in the Specification and that one of ordinary skill